

In the Specification:

Please cancel the title as filed in favor of the amended title as follows:

METHOD FOR MANUFACTURING A CAPACITOR IN A  
SEMICONDUCTOR DEVICE ~~OF FORMING MEMORY DEVICE~~

Please amend the paragraph beginning on page 3, line 15, as follows:

The stack structure is formed as follows. First, after the formation of a ~~a~~ an inter-layer insulation film ~~305~~ 140 on a semiconductor substrate ~~300~~ 100, a storage contact hole is formed and connected to an active region (not illustrated) of the semiconductor substrate through the inter-layer insulation film 140. Subsequently, a plug is molded by forming a polysilicon ~~340~~ layer 145 and a barrier layer 165 and a silicide layer, ~~315, and barrier layer 320~~ respectively. After the formation of the plug, the bottom electrode is deposited, etched selectively and thus a bottom electrode pattern ~~325~~ 170 is formed. A stack capacitor is formed by molding a dielectric layer ~~330~~ 180 and a top electrode ~~335~~ 180 on the bottom electrode pattern ~~325~~ 170 and patterning it.